

	Type	L #	Hits	Search Text	Time Stamp
1	BRS	L1	36	(RTA or (rapid adj3 thermal adj3 anneal\$3)) same before same after same electrode	2002/10/30 17:37

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TITLE: Semiconductor device with perovskite capacitor and its manufacture method

----- KWIC -----

After the PZT dielectric film 28 is deposited and before or after the upper electrode layer 29 is deposited, an annealing process in an O._{sub.2} atmosphere is performed. For example, the annealing process is performed for about 5 seconds at 850.degree. C. in an O._{sub.2} atmosphere at one atm. Such an annealing process can be performed by using a rapid thermal anneal (RTA) system. Instead of RTA, an annealing process may be performed by using a resistance heating furnace at 800.degree. C. or higher for 10 minutes or longer, for example, at 800.degree. C. for 30 minutes.